Performance

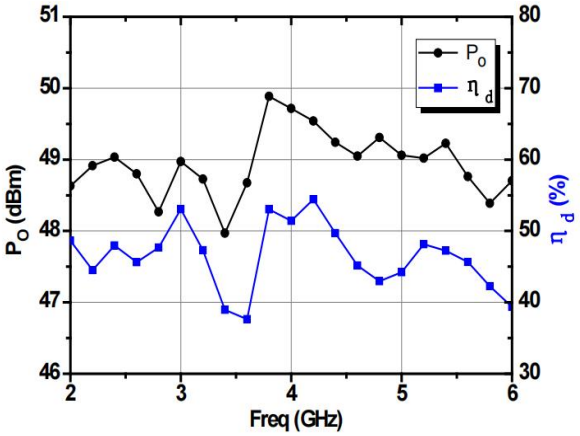
- Technology: 0.25um Power GaN HEMT
- Frequency: 2.0~6.2GHz
- Typical Pout : ≧48dBm(CW)
- Typical Gain: ≧8dB
- Typical PAE: ≧35%
- Bias: 28V@1.0A
- Package: Metal Ceramic

Electrical Specifications (T_A=25℃,V_d=28V,Idq=1A,F: 2~6.2GHz,Pin=40dBm)

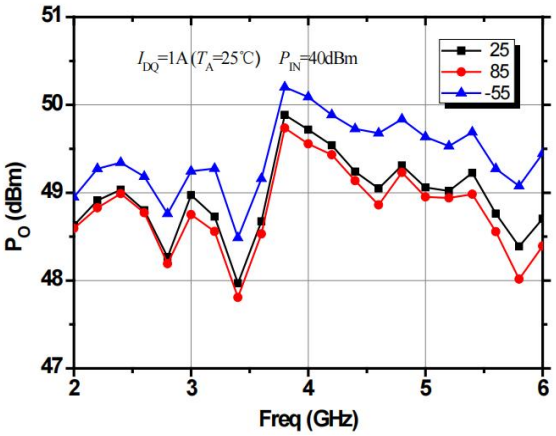
Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	48	-	-	dBm
Gp	Power Gain	8	-	-	dB
ηadd	Power Added Efficiency	35	-	-	%
△Gp	Gain Flatness	-1.0	-	+1.0	dB
Rth	Thermal Resistance	-	-	1.05	℃/W

Test Curves

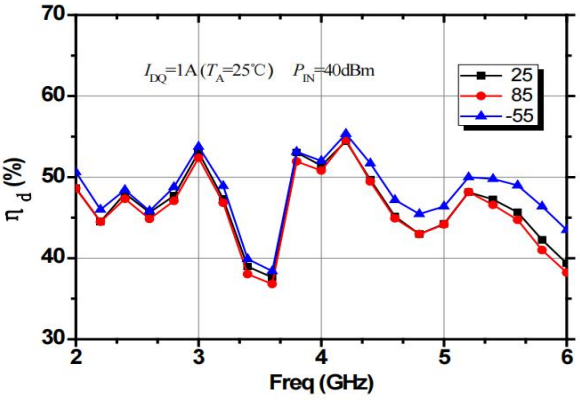
Pout、ηadd&Freq.



Pout&Freq. @ Different Temp.



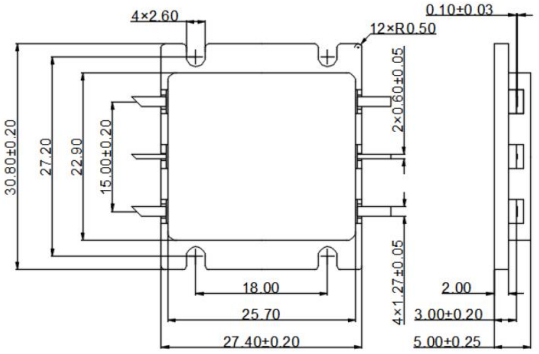
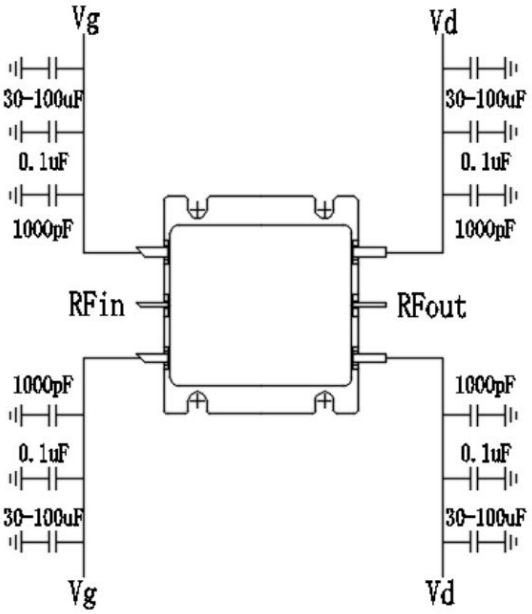
ηadd&Freq. @ Different Temp.



Absolute Max Ratings (T_A=25℃)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	40V	
Vg	Grid Voltage	-5V	
Pd	DC Power	225W	25℃
Tch	Channel Temperature	225℃	【1】
Tm	Mounting Temperature	300℃	1 min, N_2 Protection
Tstg	Storage Temperature	-55~175℃	

【1】Exceeding any one or combination of these limits may cause permanent damage.

Outline Drawing	Application Circuit
	

Note:

(1) This product is an internal matching tube, with input and output impedance values of 50 ohms;

(2) The power-on sequence shall be in strict accordance with the sequence of applying negative power first and then positive power. When power-off, the leakage voltage shall be reduced first and then the grid voltage shall be reduced;

(3) This product is a high-power device. Pay attention to heat dissipation during use. The higher the shell temperature is, the shorter the service life is. The service temperature should not be higher than 85 ℃;

(4) This product is an electrostatic sensitive device. It needs to pay attention to electrostatic protection during storage and use, and it needs to be grounded well during use;

(5) The input standing wave ratio is high, and the input end needs to adopt radio frequency isolation measures.